not formed at the side of a drain region 208 of the n-channel TFT, and this becomes a structure that prevents reduction of the operational frequency due to a parasitic capacity.--

IN THE DRAWINGS:

Corrections have been made to Figs. 7A, 8C, 10, 12A, 12C, 24A and 26C with a Request for Approval of Drawing Corrections filed concurrently herewith.

IN THE CLAIMS:

Please cancel claims 45-80 without prejudice or disclaimer of the subject matter contained therein.

Please amend claims 1, 2, 9-11, 18-20, 27, and 36 as follows. Claims 1, 2, 9-11, 18-20, 27 and 36 are presented below in their amended form. The amendments to the above-noted claims are outlined in an Attachment to the Amendment using the conventional indication method of bracketing and underlining.

1. (Amended) A semiconductor device comprising a driver circuit and a pixel section over a substrate, wherein:

a) said driver circuit includes:

a first thin film transistor comprising:

a channel forming region and a third impurity region having n-type conductivity, formed on the inside of a gate electrode; and

a first impurity region having the n-type conductivity which forms a source region or a drain region, formed on the outside of the gate electrode; and

a fifth thin film transistor comprising:

a channel forming region, and a fifth impurity region having p-type conductivity which forms a source region or a drain region; and

b) said pixel section comprises:

a fourth film transistor comprising:

a channel forming region formed on the inside of a gate electrode; and

a fourth impurity region having the n-type conductivity, and a first impurity region having the n-type conductivity which forms a source region or a drain region, formed on the outside of the gate electrode.

2. (Amended) A semiconductor device according to claim 1, wherein:

an impurity element having the n-type conductivity is included in the third impurity region and in the fourth impurity region; and

a concentration of the impurity element included in said fourth impurity region is less than a concentration of the impurity element included in said third impurity region.

9. (Amended) A semiconductor device comprising a driver circuit and a pixel section over a substrate, wherein:

a) said driver circuit comprises:

a first thin film transistor comprising:

a channel forming region and a third impurity region having n-type conductivity, formed on the inside of a gate electrode; and

a first impurity region having the n-type conductivity which forms a source region or a drain region, formed on the outside of the gate electrode;

a second thin film transistor comprising:

a channel forming region and a third impurity region having the n-type conductivity, formed on the inside of a gate electrode; and

a second impurity region having the n-type conductivity, and a first impurity region having the n-type conductivity which forms a source region or a drain region, formed on the outside of the gate electrode; and

a fifth thin film transistor comprising:

a channel forming region, and a fifth impurity region having p-type conductivity which forms a source region or a drain region; and

b) said pixel section comprises:

a fourth thin film transistor having:

a channel forming region formed on the inside of a gate electrode; and

a fourth impurity region having the n-type conductivity, and a first impurity region having the n-type conductivity which forms a source region or a drain region, formed on the outside of the gate electrode.

10. (Amended) A semiconductor device according to claim 2, wherein:

an impurity element having the n-type conductivity is included in the third impurity region and in the fourth impurity region; and

a concentration of the impurity element included in said fourth impurity region is less than a concentration of the impurity element included in said third impurity region.

11. (Amended) A semiconductor device according to claim 9, wherein:

an impurity element having the n-type conductivity is included in the second impurity region and in the third impurity region; and

a concentration of the impurity element included in said second impurity region is the same as a concentration of the impurity element included in said third impurity region.

---

18. (Amended) A semiconductor device comprising a driver circuit and a pixel section over a substrate, wherein:

a) said driver circuit comprises:

a third thin film transistor comprising:

a channel forming region formed on the inside of a gate electrode; and

a second impurity region having n-type conductivity, and a first impurity region having the n-type conductivity which forms a source region or a drain region, formed on the outside of the gate electrode; and

a fifth thin film transistor comprising:

a channel forming region, and a fifth impurity region having p-type conductivity which forms a source region or a drain region; and

b) said pixel section comprises:

a fourth thin film transistor comprising:

a channel forming region formed on the inside of a gate electrode; and

a fourth impurity region having the n-type conductivity, and a first impurity region having the n-type conductivity which forms a source region or a drain region, formed on the outside of the gate electrode.

19. (Amended) A semiconductor device according to claim 18, wherein:
a length of said second impurity region is 0.5 to 3.0 μm.

20. (Amended) A semiconductor device according to claim 18, wherein:
said third and fifth thin film transistor constitute a sampling circuit.

---

27. (Amended) A semiconductor device comprising a driver circuit and a pixel section over a substrate, wherein:

a) said driver circuit comprises:

a first thin film transistor comprising:

a channel forming region and a third impurity region having n-type conductivity, formed on the inside of a gate electrode; and

a first impurity region having the n-type conductivity which forms a source region or a drain region, formed on the outside of the gate electrode;

wherein said first thin film transistor constitutes a shift register circuit, and

a second thin film transistor comprising:

a channel forming region and the third impurity region having the n-type conductivity, formed on the inside of a gate electrode; and

a second impurity region having the n-type conductivity, and a first impurity region having the n-type conductivity which forms a source region or a drain region, formed on the outside of the gate electrode;

wherein said second thin film transistor constitutes a sampling circuit, and

b) said pixel section comprises:

a fourth thin film transistor comprising:

a channel forming region formed on the inside of a gate electrode; and

a fourth impurity region having the n-type conductivity, and a first impurity region having the n-type conductivity which forms a source region or a drain region, formed on the outside of the gate electrode.

36. (Amended) A semiconductor device having a panel comprising a pixel section and a driver circuit formed over a substrate, wherein:

a) said pixel section comprises a thin film transistor comprising:

a semiconductor layer formed over an insulating surface of said substrate;

a gate insulating film on said semiconductor layer and a gate electrode over said gate insulating film;

a channel forming region formed in said semiconductor layer;

a source region and a drain region formed in said semiconductor layer; and

a lightly doped drain (LDD) region, formed in said semiconductor layer so as not to be overlapped with said gate electrode, and

b) said driver circuit comprises:

a first thin film transistor comprising:

a first semiconductor layer formed over an insulating surface of said substrate;

a gate insulating film on said first semiconductor layer and a first gate electrode over said gate insulating film;

a first channel forming region formed in said semiconductor layer;

a first source region and a first drain region formed in said first semiconductor layer; and